



DOCUMENT CHANGE REQUEST

DCR number 1779 Changes required for: General

Date: 2026/01/12

Date sent: 2025/12/11

Originator: Steve Jeffery

Organisation: ESCC Executive Secretariat

Status: IMPLEMENTED

Title: INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS DIGITAL, MEMORY, RADIATION

Number: 9304/010

Issue: 4

Other documents affected:

Page:

Various - see attached MSWord file

Paragraph:

Various - see attached MSWord file

Original wording:

See the existing published spec: 9304/010 Issue 4.

Proposed wording:


As highlighted in the attached MSWord file "ESCC9304010Iss5 Draft B for DCR review"

Justification:

This DCR, which replaces DCR1751 [Withdrawn] (and hence the attached MSWord file is Draft B) has been raised by the T.W. on behalf of STMicroelectronics, who asked for the additional Deviations as shown in a new Appendix A (i.e. the extension of the delay period after Burn-in and Operating Life).

This new Appendix also includes 'Recommended Application Information' which has been agreed, and was requested to be added, by ESA+NanoXplore.

A new Note to Para. 1.4.2 is proposed by the T.W. on the basis that it provides useful Radiation Level validation information. Such information is already included in a number of published Detail Specs.

Attachments:
esc9304010iss5_draft_b_for_dcr_review.docx
Modifications:
N/A
Approval signature:

Date signed:
2026-01-12